

# Contents

|          |                                                                                                    |           |
|----------|----------------------------------------------------------------------------------------------------|-----------|
| <b>1</b> | <b>Introduction to Semiconductor Heterostructures</b>                                              | <b>1</b>  |
| 1.1      | Introduction                                                                                       | 1         |
| 1.2      | Electronic States of Bulk Semiconductors                                                           | 3         |
| 1.2.1    | Fundamental Concepts                                                                               | 3         |
| 1.2.2    | The $\vec{k} \cdot \vec{p}$ Method                                                                 | 8         |
| 1.3      | Envelope Function Model                                                                            | 12        |
|          | References                                                                                         | 17        |
| <b>2</b> | <b>Theory and Modelling for the Nanoscale: The <i>spds</i>*</b>                                    |           |
|          | <b>Tight Binding Approach</b>                                                                      | <b>19</b> |
| 2.1      | Introduction: A Snapshot View of Theoretical Methods for Nanosciences                              | 20        |
| 2.2      | The Empirical Tight Binding Formalism                                                              | 21        |
| 2.3      | Band Structure of Bulk Materials: From $sp^3$ to $sp^3 d^5 s^*$                                    | 22        |
| 2.4      | Strain Effects: The Tight Binding Point of View                                                    | 24        |
| 2.5      | Tight Binding as a Parameter Provider: Inversion Asymmetry and Parameters of the 14-Band k.p Model | 25        |
| 2.6      | Quantum Confinement and Atomistic Symmetries: Interface Rotational Symmetry Breakdown              | 26        |
| 2.7      | Quantum Confinement and Valley Mixing: X-valley and L-valley Quantum Wells                         | 28        |
| 2.8      | Three-Dimensional Confinement: Symmetry Mistake in Current Theories of Impurity States             | 29        |
| 2.9      | Alloys, Beyond the Virtual Crystal Approximation: Dilute Nitrides                                  | 31        |
| 2.10     | Full-Band Calculations: Dielectric Function and Piezo-Optical Constants                            | 32        |
| 2.11     | Surface Physics and Modeling of STM Images                                                         | 34        |

|          |                                                                               |           |
|----------|-------------------------------------------------------------------------------|-----------|
| 2.12     | Back to Theory: Local Wavefunction<br>in the Tight Binding Approach . . . . . | 36        |
| 2.13     | Conclusion . . . . .                                                          | 38        |
|          | References . . . . .                                                          | 38        |
| <b>3</b> | <b>Theory of Electronic Transport in Nanostructures . . . . .</b>             | <b>41</b> |
| 3.1      | Introduction. . . . .                                                         | 41        |
| 3.1.1    | Scope and Overview . . . . .                                                  | 42        |
| 3.2      | Macroscopic Transport Models . . . . .                                        | 43        |
| 3.2.1    | Carrier Effective Mass . . . . .                                              | 43        |
| 3.2.2    | Carrier Mobility . . . . .                                                    | 46        |
| 3.2.3    | Carrier Scattering Mechanisms . . . . .                                       | 47        |
| 3.2.4    | Carrier Scattering Rates and Boltzmann<br>Transport Equation . . . . .        | 48        |
| 3.2.5    | Mobility in Bulk Semiconductors<br>and Heterostructures. . . . .              | 49        |
| 3.3      | Scattering in Dilute Nitrides: Beyond Fermi's Golden Rule . . .               | 51        |
| 3.4      | Quantum Hall effect. . . . .                                                  | 54        |
| 3.5      | Spin Quantum Hall Effect. . . . .                                             | 57        |
| 3.6      | Quantised Conduction Through Wires and Dots. . . . .                          | 60        |
| 3.7      | Graphene . . . . .                                                            | 62        |
| 3.8      | Junctionless Transistor . . . . .                                             | 66        |
| 3.9      | Summary and Conclusions . . . . .                                             | 67        |
|          | References . . . . .                                                          | 68        |
| <b>4</b> | <b>Hot Electron Transport . . . . .</b>                                       | <b>71</b> |
| 4.1      | Introduction. . . . .                                                         | 71        |
| 4.1.1    | The Lattice Temperature $T_0$ . . . . .                                       | 72        |
| 4.1.2    | Electrons in Thermal Equilibrium . . . . .                                    | 73        |
| 4.1.3    | Hot Electrons . . . . .                                                       | 73        |
| 4.1.4    | Scope and Overview . . . . .                                                  | 73        |
| 4.2      | Basic Concepts . . . . .                                                      | 74        |
| 4.2.1    | Ballistic Transport . . . . .                                                 | 74        |
| 4.2.2    | Energy and Momentum Relaxation . . . . .                                      | 75        |
| 4.2.3    | Describing Energy Bands . . . . .                                             | 77        |
| 4.2.4    | Group Velocity and the Density of States. . . . .                             | 80        |
| 4.2.5    | The Non-Equilibrium Distribution Function . . . . .                           | 81        |
| 4.2.6    | Transport Properties. . . . .                                                 | 82        |
| 4.2.7    | The Conservation Equations . . . . .                                          | 83        |
| 4.3      | Scattering Mechanisms . . . . .                                               | 86        |
| 4.3.1    | General Comments . . . . .                                                    | 86        |
| 4.3.2    | Electron–Electron Scattering. . . . .                                         | 87        |
| 4.3.3    | Alloy Scattering . . . . .                                                    | 88        |
| 4.3.4    | Phonons . . . . .                                                             | 90        |

|          |                                                                                                                                       |            |
|----------|---------------------------------------------------------------------------------------------------------------------------------------|------------|
| 4.4      | High-Field Phenomena . . . . .                                                                                                        | 95         |
| 4.4.1    | Impact Ionisation and Avalanche Breakdown . . . . .                                                                                   | 95         |
| 4.4.2    | Negative Differential Resistance . . . . .                                                                                            | 98         |
| 4.5      | The Boltzmann Transport Equation . . . . .                                                                                            | 101        |
| 4.5.1    | General Form of the BTE . . . . .                                                                                                     | 101        |
| 4.5.2    | The Linearized Distribution Function . . . . .                                                                                        | 102        |
| 4.5.3    | Low Field Solution and the Ladder Method . . . . .                                                                                    | 103        |
| 4.5.4    | High-Field Solution . . . . .                                                                                                         | 108        |
|          | References . . . . .                                                                                                                  | 112        |
| <b>5</b> | <b>Monte Carlo Techniques for Carrier Transport<br/>in Semiconductor Materials . . . . .</b>                                          | <b>115</b> |
| 5.1      | Introduction to Monte Carlo . . . . .                                                                                                 | 115        |
| 5.1.1    | Historical Review . . . . .                                                                                                           | 116        |
| 5.1.2    | Simple Examples of Monte Carlo . . . . .                                                                                              | 116        |
| 5.2      | Carrier Transport in Semiconductors . . . . .                                                                                         | 119        |
| 5.3      | Single Electron Monte Carlo . . . . .                                                                                                 | 121        |
| 5.3.1    | Scattering Processes . . . . .                                                                                                        | 121        |
| 5.3.2    | Drift Process . . . . .                                                                                                               | 123        |
| 5.3.3    | Description of the Algorithm . . . . .                                                                                                | 126        |
| 5.4      | Ensemble Electron Monte Carlo . . . . .                                                                                               | 137        |
| 5.4.1    | Description of the Algorithm . . . . .                                                                                                | 137        |
| 5.5      | An Example: Electron Motion in Bulk GaAs . . . . .                                                                                    | 139        |
| 5.6      | Monte Carlo Simulation at Very High Fields . . . . .                                                                                  | 142        |
| 5.7      | Electron Transport in Dilute Nitrides . . . . .                                                                                       | 144        |
| 5.7.1    | Single Electron Monte Carlo in GaAsN . . . . .                                                                                        | 145        |
| 5.8      | Quantum Monte Carlo . . . . .                                                                                                         | 147        |
| 5.9      | Appendix: Random and Pseudorandom Numbers . . . . .                                                                                   | 149        |
|          | References . . . . .                                                                                                                  | 150        |
| <b>6</b> | <b>Band Structure Engineering of Semiconductor Devices<br/>for Optical Telecommunications . . . . .</b>                               | <b>153</b> |
| 6.1      | Basics of Band Structure Engineering . . . . .                                                                                        | 153        |
| 6.1.1    | What is a Strained Semiconductor Layer? . . . . .                                                                                     | 154        |
| 6.1.2    | Main Disadvantages of Lattice Matched III–V<br>Semiconductor Lasers and Solutions Proposed<br>by Band-Structure Engineering . . . . . | 156        |
| 6.2      | Effects of Strain on the Band Structure . . . . .                                                                                     | 159        |
| 6.2.1    | Bulk InGaAs Under Biaxial Compression . . . . .                                                                                       | 159        |
| 6.2.2    | Electronic Band Structure in Strained<br>Quantum Wells . . . . .                                                                      | 162        |
| 6.2.3    | Influence of Strain on the Loss Mechanisms . . . . .                                                                                  | 168        |
| 6.2.4    | Strain-Induced Changes of the Laser<br>Threshold Current . . . . .                                                                    | 172        |

|          |                                                                      |            |
|----------|----------------------------------------------------------------------|------------|
| 6.3      | Gain Calculation in $\text{III-V}$ Quantum Wells . . . . .           | 173        |
| 6.3.1    | Device Geometry. . . . .                                             | 173        |
| 6.3.2    | Carrier Wavefunctions in Quantum Wells. . . . .                      | 174        |
| 6.3.3    | Light-Matter Interaction and Optical Selection Rules. . .            | 174        |
| 6.3.4    | Gain Calculation . . . . .                                           | 176        |
| 6.4      | Uncooled Operation of 1.3 $\mu\text{m}$ Lasers . . . . .             | 177        |
| 6.4.1    | Conduction Band of InGaAsN. . . . .                                  | 178        |
| 6.4.2    | Gain Improvement of InGaAsN Structures<br>is Obtained by . . . . .   | 180        |
| 6.5      | Large Bandwidth Semiconductor Optical Amplifiers . . . . .           | 184        |
| 6.5.1    | InGaAsP/InP Heterostructures. . . . .                                | 184        |
| 6.5.2    | How to Realize Polarisation-Independent Gain? . . . . .              | 185        |
| 6.5.3    | How to Increase Bandwidth?. . . . .                                  | 187        |
| 6.5.4    | Band Structure and Gain . . . . .                                    | 189        |
|          | References . . . . .                                                 | 192        |
| <b>7</b> | <b>Fundamental Theory of Semiconductor Lasers and SOAs . . . . .</b> | <b>195</b> |
| 7.1      | Review of Key Concepts . . . . .                                     | 195        |
| 7.1.1    | Radiative Transitions . . . . .                                      | 196        |
| 7.1.2    | Spontaneous and Stimulated Emission . . . . .                        | 196        |
| 7.1.3    | Optical Gain . . . . .                                               | 197        |
| 7.2      | Semiconductor Laser Structures. . . . .                              | 199        |
| 7.2.1    | Heterostructures. . . . .                                            | 199        |
| 7.2.2    | Optical Waveguides. . . . .                                          | 200        |
| 7.3      | Semiconductor Laser Cavities . . . . .                               | 202        |
| 7.3.1    | Fabry-Perot Cavity. . . . .                                          | 202        |
| 7.3.2    | Lasing Threshold and Power Output . . . . .                          | 204        |
| 7.3.3    | Distributed Bragg Reflectors. . . . .                                | 205        |
| 7.3.4    | Distributed Feedback Lasers . . . . .                                | 207        |
| 7.4      | Transient Behaviour of Lasers. . . . .                               | 209        |
| 7.4.1    | Static Properties . . . . .                                          | 209        |
| 7.4.2    | Rate Equations . . . . .                                             | 209        |
| 7.4.3    | Small-Signal Modulation . . . . .                                    | 210        |
| 7.4.4    | Large-Signal Modulation . . . . .                                    | 212        |
| 7.4.5    | Chirp . . . . .                                                      | 214        |
| 7.5      | Semiconductor Optical Amplifiers . . . . .                           | 215        |
| 7.5.1    | Cavity Effects . . . . .                                             | 215        |
| 7.5.2    | Saturation . . . . .                                                 | 217        |
| 7.5.3    | Crosstalk . . . . .                                                  | 218        |
| 7.5.4    | Polarisation. . . . .                                                | 220        |
| 7.6      | Conclusion . . . . .                                                 | 221        |
|          | References . . . . .                                                 | 222        |

|          |                                                          |            |
|----------|----------------------------------------------------------|------------|
| <b>8</b> | <b>Vertical Cavities and Micro-Ring Resonators</b>       | <b>225</b> |
| 8.1      | Introduction                                             | 225        |
| 8.2      | Vertical Cavities                                        | 227        |
| 8.2.1    | Basic Design Concepts                                    | 227        |
| 8.2.2    | Optical Feedback and DBRs                                | 229        |
| 8.2.3    | Material Gain                                            | 232        |
| 8.2.4    | The Gain Enhancement Factor                              | 232        |
| 8.2.5    | Vertical Cavity Semiconductor Optical Amplifiers (VCSOA) | 234        |
| 8.2.6    | VCSEL Polarisation Properties and Spin-VCSELs            | 237        |
| 8.3      | Microring Resonators                                     | 240        |
| 8.3.1    | Fundamental Concepts                                     | 240        |
| 8.3.2    | Waveguiding Properties of Micro Ring Resonators          | 243        |
| 8.3.3    | Single and Multi-Micro Ring Configurations               | 244        |
| 8.3.4    | Active Micro Ring Structures                             | 248        |
| 8.4      | Conclusion                                               | 252        |
|          | References                                               | 253        |
|          | <b>Index</b>                                             | <b>255</b> |